

Abstract

A diode includes a semiconductor substrate that is situated between two metallic electrodes (5,6), having a strongly doped first zone (3) that forms an ohmic transition to the first electrode (6), a weakly doped second zone (1), having the same conductivity type, that forms a rectifying transition to the second electrode (5), and a third zone (2) that, having the same conductivity type, is doped more weakly than the second zone (3); the third zone (2) separates the first and the second zones (1,3) from one another, and the second zone (1) is enclosed between the second electrode (5) and the third zone (2).

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